

## Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

[International Rectifier \(Infineon Technologies Americas Corp.\)  
IRFPS3815PBF](#)

For any questions, you can email us directly:

[sales@integrated-circuit.com](mailto:sales@integrated-circuit.com)

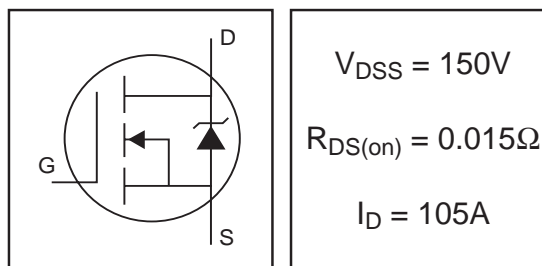
International  
**IR** Rectifier

PD - 95896

# IRFPS3815PbF

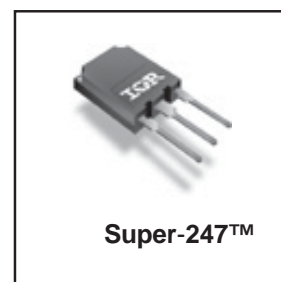
HEXFET<sup>®</sup> Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



## Description

The HEXFET<sup>®</sup> Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.



## Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	105	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	74	
$I_{DM}$	Pulsed Drain Current ①	390	
$P_D @ T_C = 25^\circ C$	Power Dissipation	441	W
	Linear Derating Factor	2.9	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulse Avalanche Energy ②	1610	mJ
$I_{AR}$	Avalanche Current ①	58	A
$E_{AR}$	Repetitive Avalanche Energy ①	38	mJ
dv/dt	Peak Diode Recovery dv/dt ③	3.0	V/ns
$T_J$	Operating Junction and	-55 to + 175	
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.34	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient	—	40	

www.irf.com

1

09/13/04

# IRFPS3815PbF

 International  
**IR** Rectifier

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	150	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient	—	0.18	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	0.015	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 63A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	3.0	—	5.0	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	47	—	—	S	V <sub>DS</sub> = 50V, I <sub>D</sub> = 58A
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 30V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -30V
Q <sub>g</sub>	Total Gate Charge	—	260	390	nC	I <sub>D</sub> = 58A
Q <sub>gs</sub>	Gate-to-Source Charge	—	53	80		V <sub>DS</sub> = 120V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	150	230		V <sub>GS</sub> = 10V ④
t <sub>d(on)</sub>	Turn-On Delay Time	—	22	—	ns	V <sub>DD</sub> = 75V
t <sub>r</sub>	Rise Time	—	130	—		I <sub>D</sub> = 58A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	51	—		R <sub>G</sub> = 1.03Ω
t <sub>f</sub>	Fall Time	—	60	—		V <sub>GS</sub> = 10V ④
L <sub>D</sub>	Internal Drain Inductance	—	5.0	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L <sub>S</sub>	Internal Source Inductance	—	13	—		
C <sub>iss</sub>	Input Capacitance	—	6810	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	1570	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	480	—		f = 1.0MHz, See Fig. 5
C <sub>oss</sub>	Output Capacitance	—	9820	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 1.0V, f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	670	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 120V, f = 1.0MHz
C <sub>oss eff.</sub>	Effective Output Capacitance ⑤	—	1270	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 120V

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	105	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	390		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 58A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	270	410	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 58A
Q <sub>rr</sub>	Reverse Recovery Charge	—	2990	4490	nC	di/dt = 100A/μs ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

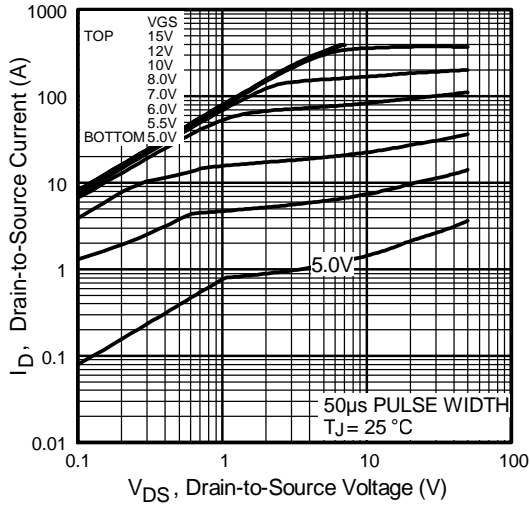
### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting T<sub>J</sub> = 25°C, L = 0.96mH  
R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 58A. (See Figure 12)
- ③ I<sub>SD</sub> ≤ 58A, di/dt ≤ 450A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>,  
T<sub>J</sub> ≤ 175°C

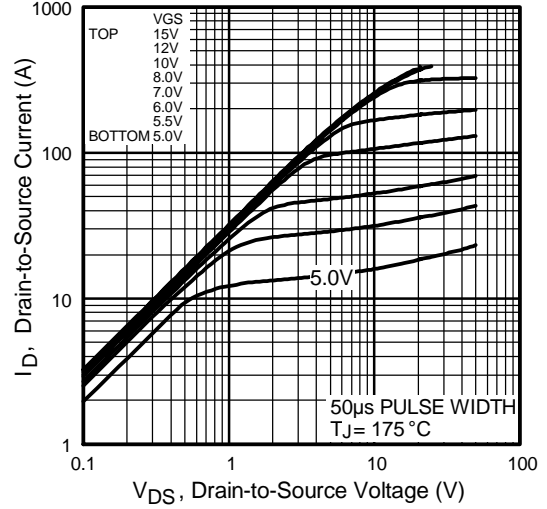
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ C<sub>oss eff.</sub> is a fixed capacitance that gives the same charging time as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 to 80% V<sub>DS</sub>

International  
**IR** Rectifier

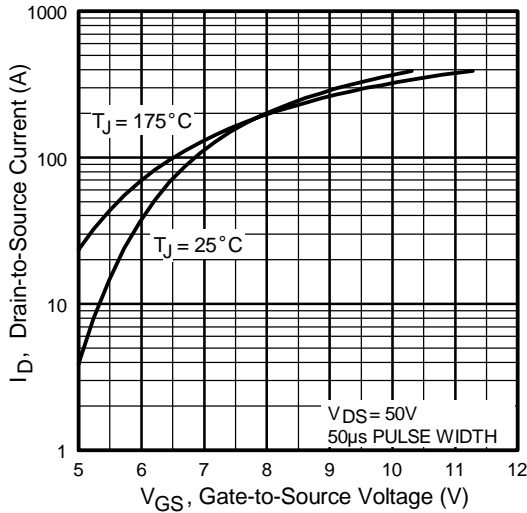
# IRFPS3815PbF



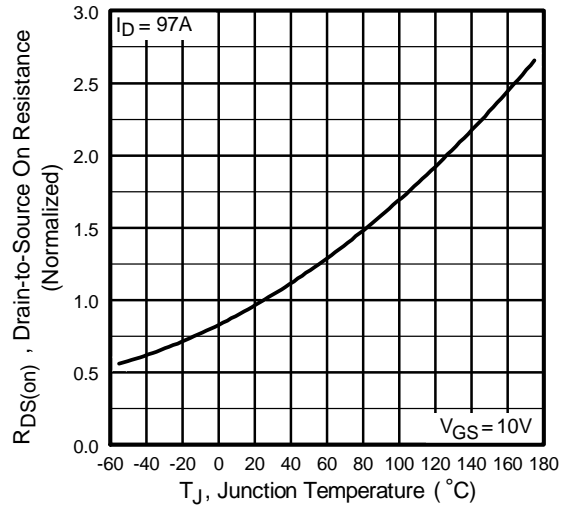
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics



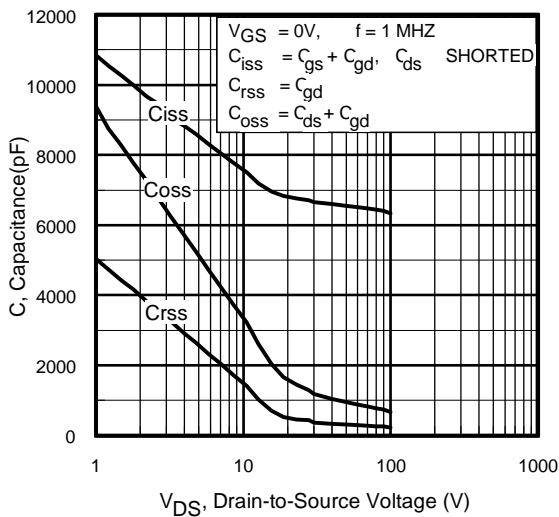
**Fig 3.** Typical Transfer Characteristics



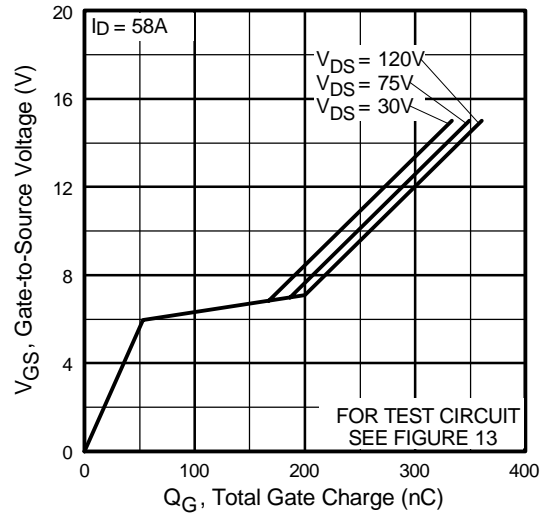
**Fig 4.** Normalized On-Resistance Vs. Temperature

# IRFPS3815PbF

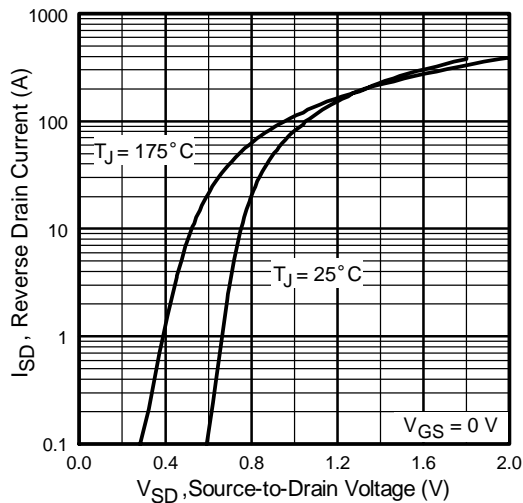
International  
**IR** Rectifier



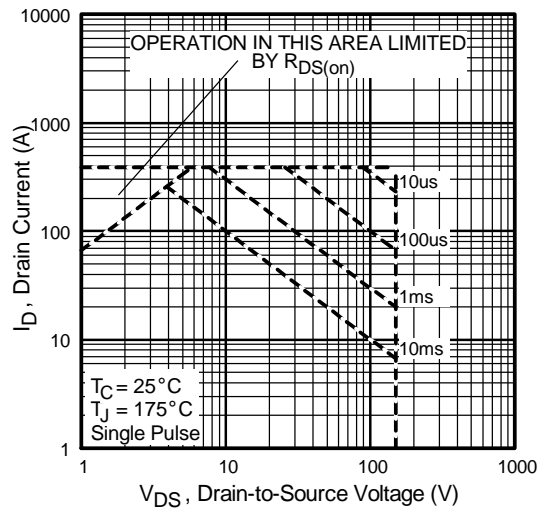
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



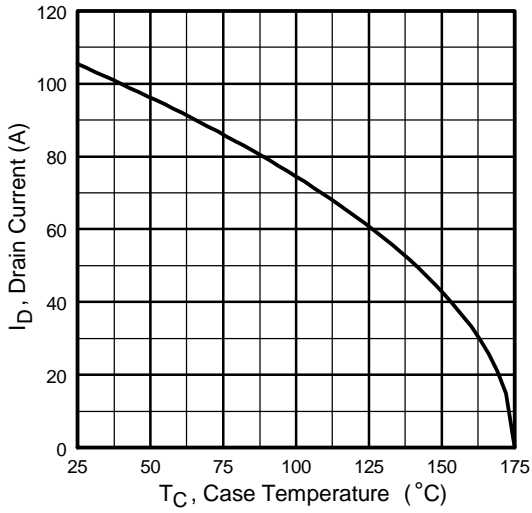
**Fig 7.** Typical Source-Drain Diode Forward Voltage



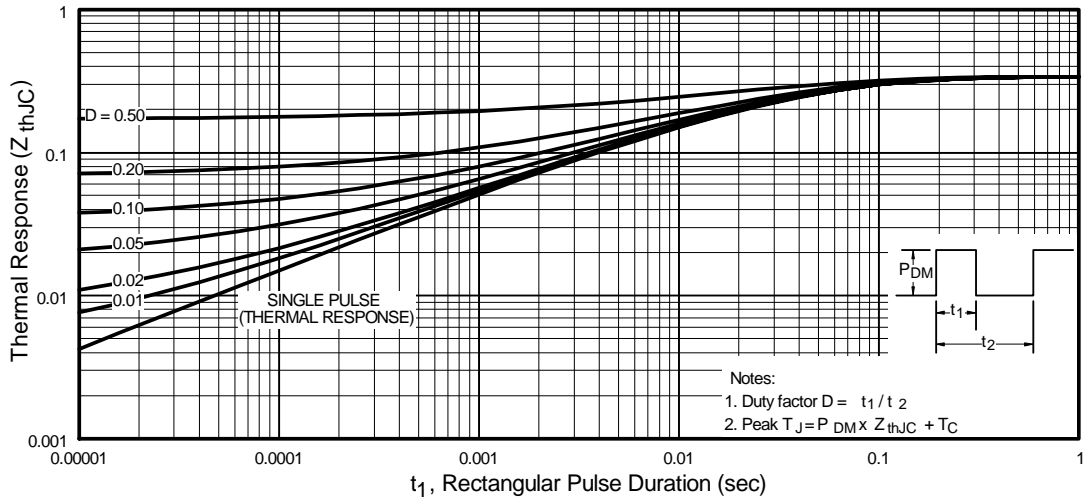
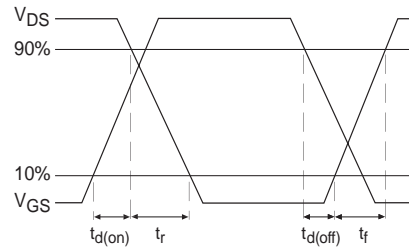
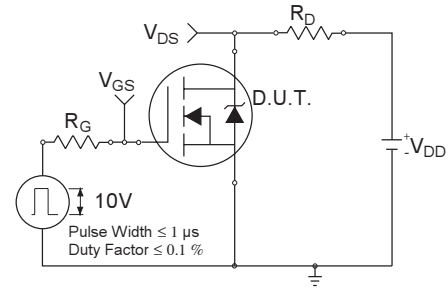
**Fig 8.** Maximum Safe Operating Area

International  
**IR** Rectifier

# IRFPS3815PbF



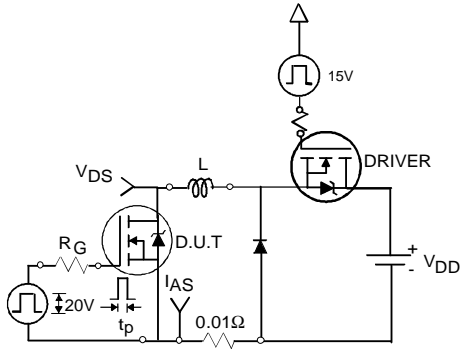
**Fig 9.** Maximum Drain Current Vs. Case Temperature



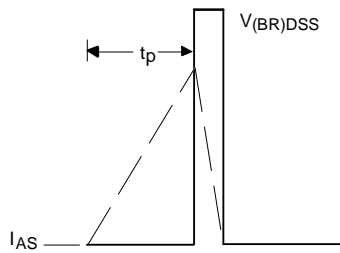
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

# IRFPS3815PbF

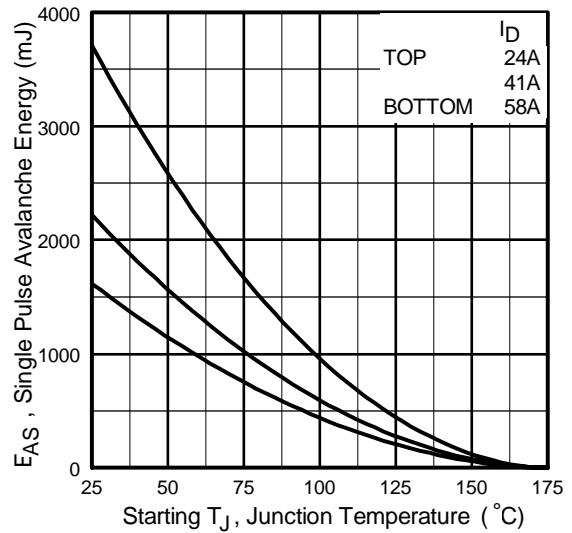
International  
**IR** Rectifier



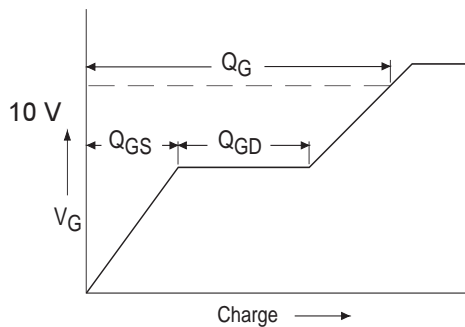
**Fig 12a.** Unclamped Inductive Test Circuit



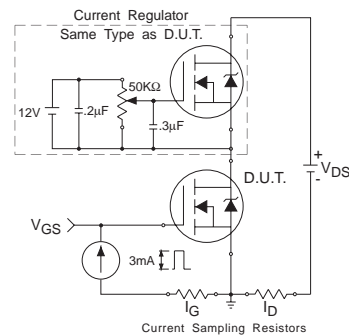
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



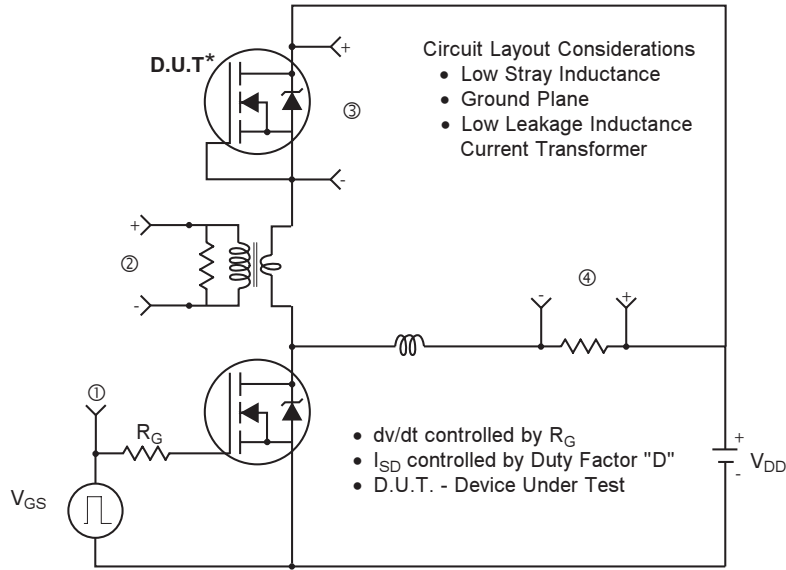
**Fig 13a.** Basic Gate Charge Waveform



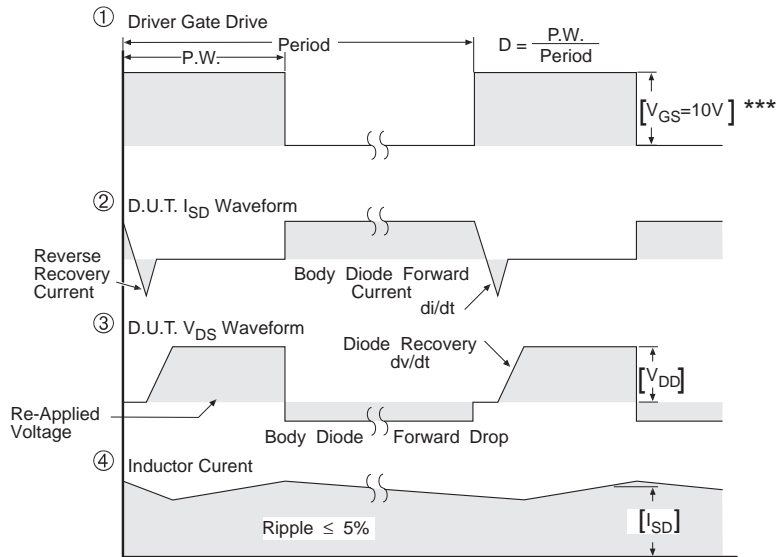
**Fig 13b.** Gate Charge Test Circuit

# IRFPS3815PbF

## Peak Diode Recovery dv/dt Test Circuit



\* Reverse Polarity of D.U.T for P-Channel



\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

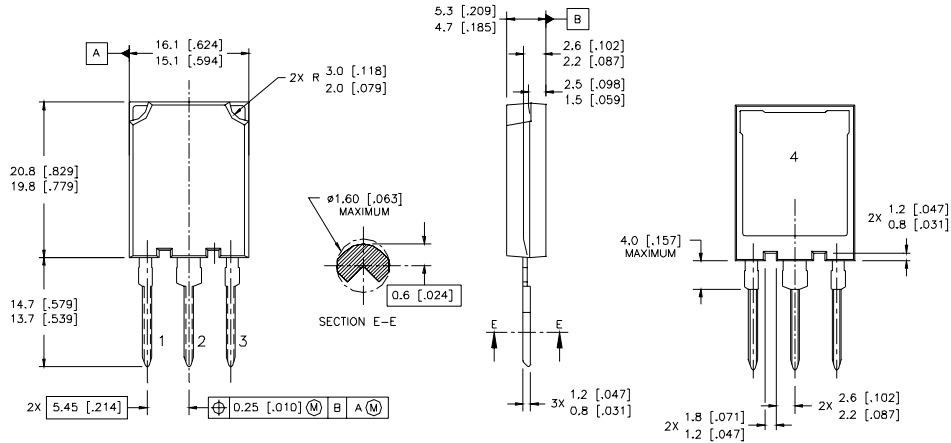
**Fig 14.** For N-channel HEXFET® power MOSFETs



# IRFPS3815PbF

## Case Outline and Dimensions — Super-247

International  
**IR** Rectifier

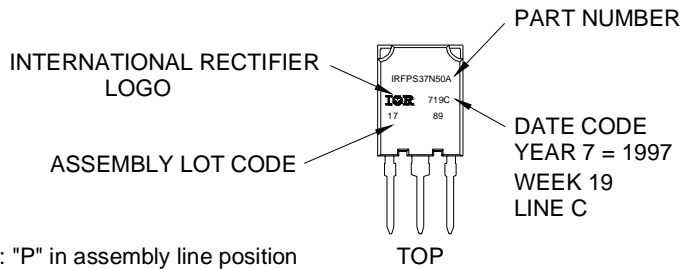


NOTES:  
 1. DIMENSIONS & TOLERANCING PER ASME Y14.5M-1994  
 2. CONTROLLING DIMENSION: MILLIMETER  
 3. DIMENSIONS ARE SHOWN IN MILLIMETRES [INCHES]

LEAD ASSIGNMENTS	
MOSFET	IGBT
1 - GATE	1 - GATE
2 - DRAIN	2 - COLLECTOR
3 - SOURCE	3 - EMITTER
4 - DRAIN	4 - COLLECTOR

## Super-247 (TO-274AA) Part Marking Information

EXAMPLE: THIS IS AN IRFPS37N50A WITH  
 ASSEMBLY LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"



Note: "P" in assembly line position indicates "Lead-Free"

Data and specifications subject to change without notice.  
 This product has been designed and qualified for the industrial market.  
 Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
 TAC Fax: (310) 252-7903

Visit us at [www.irf.com](http://www.irf.com) for sales contact information. 09/04

[www.irf.com](http://www.irf.com)